

BUK9230-100B

N-channel TrenchMOS logic level FET Rev. 02 — 1 February 2011

Product data sheet

1. **Product profile**

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 185 °C rating

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 185 °C	-	-	100	V
I _D	drain current	$V_{GS} = 5 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	47	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	167	W
Static cha	aracteristics					
R_{DSon}	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	24	28	mΩ
	resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 9; see Figure 13	-	25	30	mΩ
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_D = 47 \text{ A}; V_{\text{sup}} \le 100 \text{ V};$ $R_{\text{GS}} = 50 \Omega; V_{\text{GS}} = 5 \text{ V};$ $T_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}$	-	-	150	mJ
Dynamic	Dynamic characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 80 \text{ V};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 10}}{\text{ V}}$	-	13	-	nC



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2. Pinning information

Table 2. Pinning information

	-			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D
3	S	source		
mb D	D	mounting base; connected to drain	1 3	mbb076 S
			SOT428 (DPAK)	

^[1] It is not possible to make a connection to pin 2 of the SOT428 package.

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
BUK9230-100B	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Cumbal	Davamatas	Canditions	NA:	Mass	11
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 185 °C	-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-15	15	V
I _D	drain current	T_{mb} = 100 °C; V_{GS} = 5 V; see <u>Figure 1</u>	-	33	Α
		T_{mb} = 25 °C; V_{GS} = 5 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	47	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; see Figure 3	-	185	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	167	W
T _{stg}	storage temperature		-55	185	°C
Tj	junction temperature		-55	185	°C
Source-drain	diode				
Is	source current	T _{mb} = 25 °C	-	47	Α
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C	-	185	Α
Avalanche rug	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 47 A; V_{sup} ≤ 100 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped	-	150	mJ

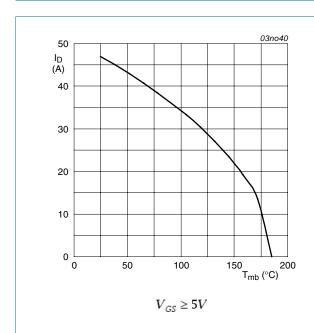


Fig 1. Continuous drain current as a function of mounting base temperature

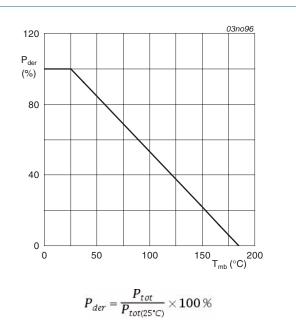
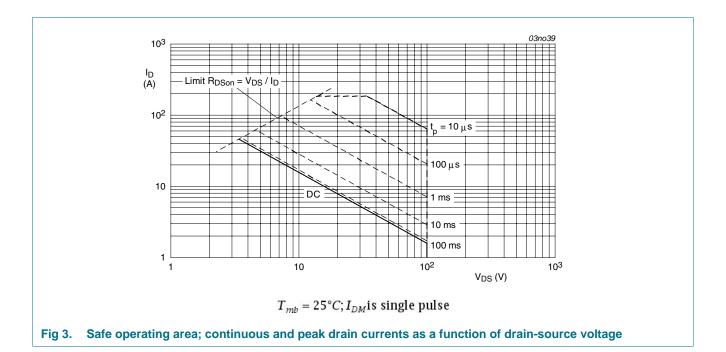


Fig 2. Normalized total power dissipation as a function of mounting base temperature

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.95	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	71.4	-	K/W

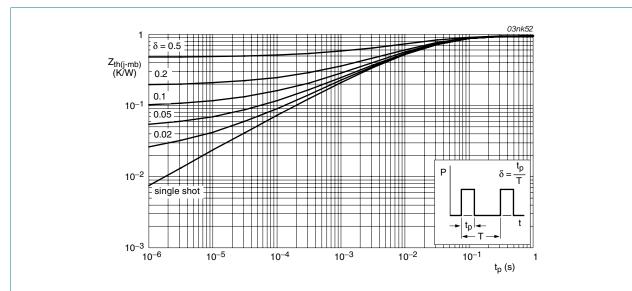


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS} drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V	
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 185 \text{ °C}$; see Figure 8	0.4	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see Figure 8	1.1	1.5	2	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 8	-	-	2.3	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 185 ^{\circ}\text{C}$	-	-	500	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	1	μA
I _{GSS}	gate leakage current	V _{GS} = 15 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		$V_{GS} = -15 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 185 °C;$ see <u>Figure 9</u> ; see <u>Figure 13</u>	-	-	78	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	24	28	$m\Omega$
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	-	33	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 9</u> ; see <u>Figure 13</u>	-	25	30	mΩ
Dynamic	characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$	-	33	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 10</u>	-	7	-	nC
Q_{GD}	gate-drain charge		-	13	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	2854	3805	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 11</u>	-	232	278	pF
C_{rss}	reverse transfer capacitance		-	81	110	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	30	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	86	-	ns
t _{d(off)}	turn-off delay time		-	96	-	ns
t _f	fall time		-	46	-	ns
L _D	internal drain inductance	measured from drain to center of die ; $T_j = 25~^{\circ}\text{C}$	-	2.5	-	nΗ
L _S	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nΗ
Source-d	rain diode					
		$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_i = 25 \text{ °C};$	-	0.85	1.2	V
V_{SD}	source-drain voltage	see <u>Figure 12</u>		0.00		
V_{SD}	source-drain voltage reverse recovery time		-	114	-	ns

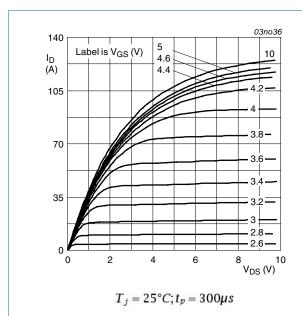


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

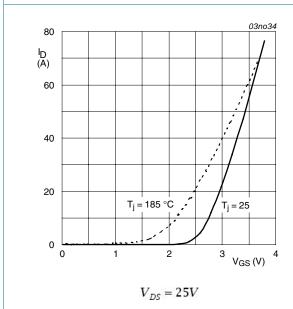
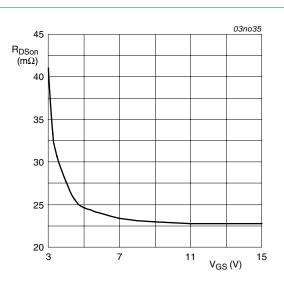
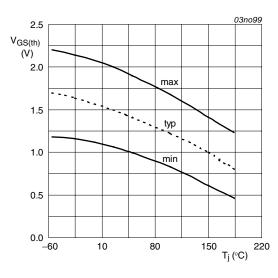


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25^{\circ}C; I_D = 25A$

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $I_D = 1mA; V_{DS} = V_{GS}$

Fig 8. Gate-source threshold voltage as a function of junction temperature

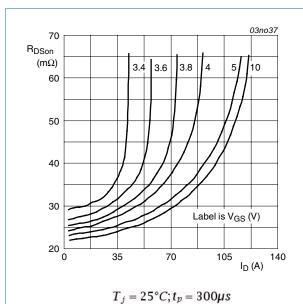
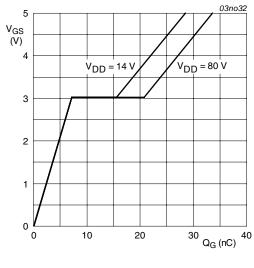


Fig 9. Drain-source on-state resistance as a function of drain current; typical values



 $T_j = 25^{\circ}C; I_D = 25A$

Fig 10. Gate-source voltage as a function of gate charge; typical values

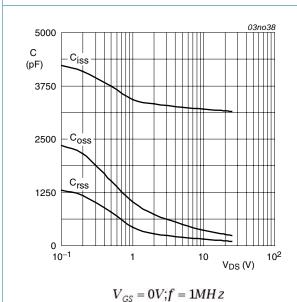


Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

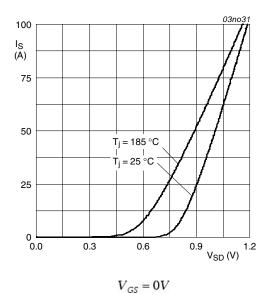


Fig 12. Source current as a function of source-drain voltage; typical values

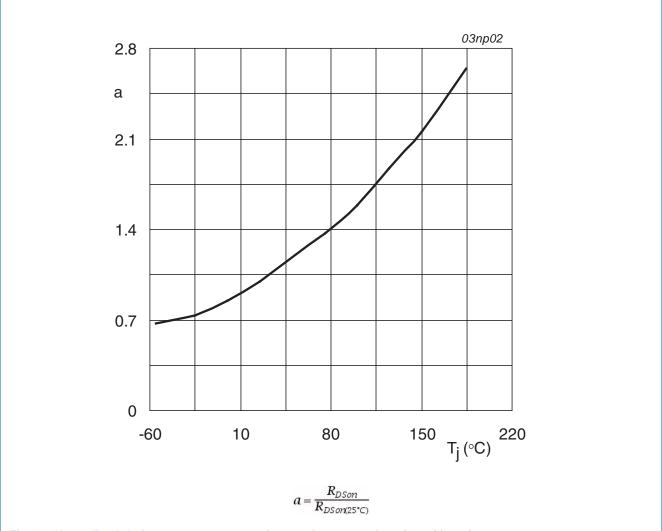


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

7. Package outline

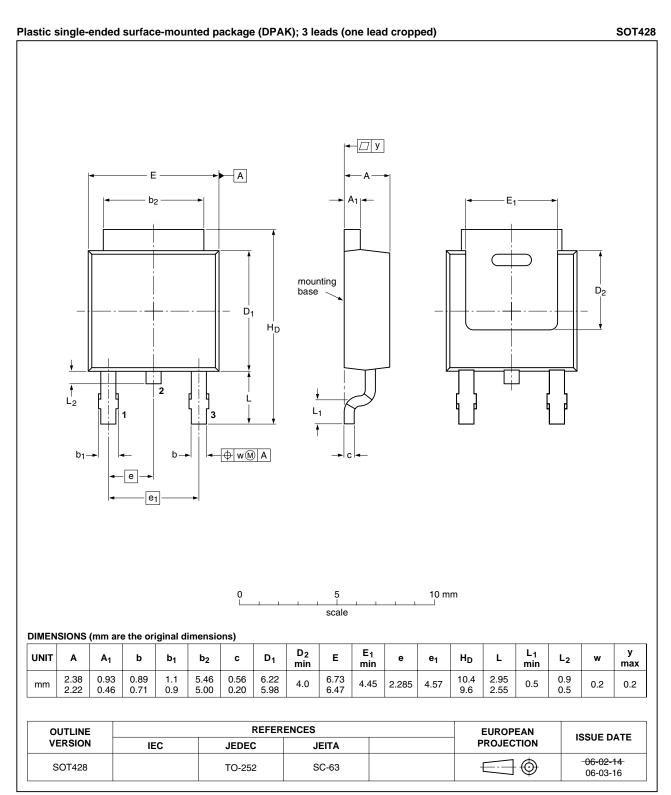


Fig 14. Package outline SOT428 (DPAK)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9230-100B v.2	20110201	Product data sheet	-	BUK9230_100B v.1
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guide of NXP Semiconductors. 		the new identity guidelines	
	 Legal texts ha 	ve been adapted to the new	company name where	appropriate.
BUK9230_100B v.1	20040122	Product data	-	-

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9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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